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270mA 5.0kV 70nS - High Voltage Surface Mount Diodes

SHAPE DISPLAY:

HVGT high voltage silicon rectifier diodes is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

### **FEATURES:**

- 1. High reliability design.
- 2. High voltage design.
- 3. High frequency , Fast Recovery.
- 4. Conform to RoHS.
- 5. Epoxy resin molded in vacuumHave anticorrosion in the surface.
- 6. Surface Mount.

### **APPLICATIONS:**

- 1. High voltage multiplier circuit
- 2. High current and high voltage circuit.
- 3. General purpose high voltage rectifier.
- 4. Medical X-ray machine HV power supply.

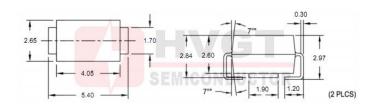
### **MECHANICAL DATA:**

- 1. Case: epoxy resin molding.
- 2. Terminal: welding axis.
- 3. Minimum packing quantity: 3,000pcs.

SIZE: (Unit:mm)

HVGT NAME: SMA-J

### **SMA-J Series** Sma-J Lead



Unit:mm

### MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings) **Data Value Symbols** Condition Units Items **Repetitive Peak Renerse Voltage** VRRM Ta=25°C; 5.0 kV 270 Average Output Current IF Ta=55°C; Resistive Load mA Suege Current IFSM Ta=25°C; 1/2 Sine(60Hz); 8.3mS 10 А -40~+125 °C Junction Temperature Τı Allowable Operation Case Temperature Тс 125 °C -40~+125 °C Storage Temperature TSTG

## **ELECTRICAL CHARACTERISTICS:** Ta=25°C (Unless otherwise specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	VF	at 25°C;I <sub>F</sub> =100mA	8.5	V
Maximum Reverse Current	Ir1	at 25°C;Vr =Vrrm	0.5	uA
	Ir2	at 100°C;V <sub>R</sub> =V <sub>RRM</sub>	10	uA
Maximum Reverse Recovery Time	Trr	at 25°С; If=0.5Ir; Ir=Ifavm; Irr=0.25Ir	75	nS
Junction Capacitance	CJ	at 25°C; V <sub>R</sub> =0V; f=1MHz	4.5	pF





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